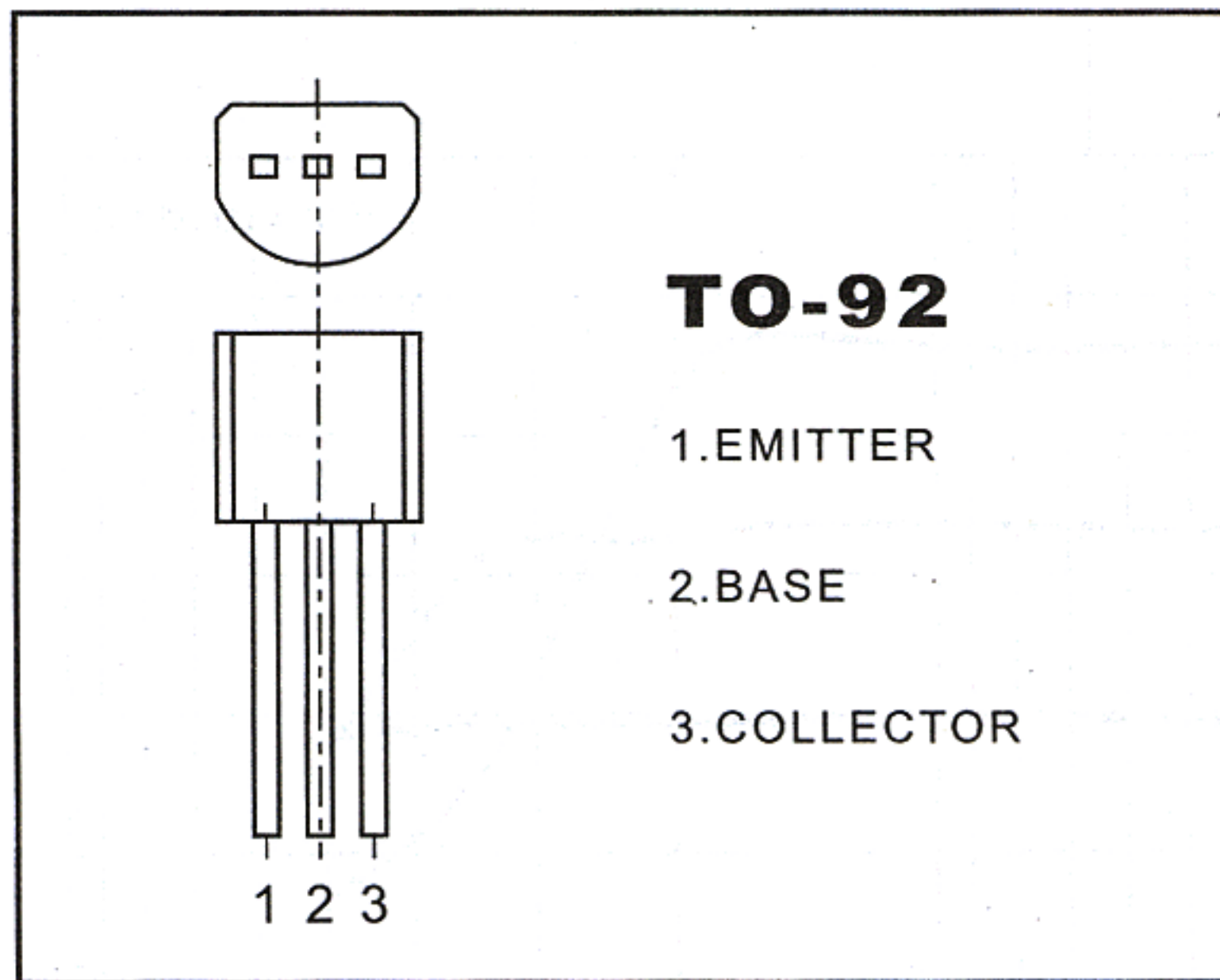


TO-92 Plastic-Encapsulate Transistors

A92 TRANSISTOR(PNP)



FEATURES

Power dissipation

P_{CM} : 0.625W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.5 A

Collector-base voltage

$V_{(BR)CBO}$: -300V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu A, I_E = 0$	-300		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 mA, I_B = 0$	-300		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10 \mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -200 V, I_E = 0$		-0.25	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3 V, I_C = 0$		-0.25	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -10 V, I_C = -1 mA$	25		
	$h_{FE(2)}$	$V_{CE} = -10 V, I_C = -10 mA$	80	250	
	$h_{FE(3)}$	$V_{CE} = -10 V, I_C = -50 mA$	25		
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -20 mA, I_B = -2 mA$		-0.5	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = -20 mA, I_B = -2 mA$		-0.9	V
Transition frequency	f_T	$V_{CE} = -5 V, I_C = -10 mA$ $f = 30 MHz$	50		MHz

CLASSIFICATION OF $h_{FE(2)}$

Rank	A	B1	B2	C
Range	80-100	100-150	150-200	200-250

